

TLE4959C FX Flexible Transmission Speed Sensor



Features

- Hall based differential speed sensor
- High magnetic sensitivity
- Large operating airgap
- Dynamic self-calibration principle
- Adaptive hysteresis
- Output protocols with and without direction of rotation detection
- High vibration suppression capabilities
- Three wire voltage interface
- Magnetic encoder and ferromagnetic wheel application
- High immunity against ESD, EMC and mechanical stress, improved voltage dropout capability
- Automotive operating temperature range
- End-of-line programmable to adjust transmission requirements.
- Green Product (RoHS compliant)
- AEC Qualified

Applications

The TLE4959C FX is an integrated differential Hall speed sensor ideally suited for transmission applications. Its basic function is to provide information about rotational speed and direction of rotation to the transmission control unit. TLE4959C FX includes a sophisticated algorithm which actively suppresses vibration while keeping excellent airgap performance.

Table 1 Description

Туре	Marking	Ordering Code	Package
TLE4959C FX	59AIC1	SP001040492	PG-SSO-3-52



Description

The TLE4959C FX comes in a RoHs compliant three-pin package, qualified for automotive usage. It has two integrated capacitors on the lead frame (220 nF/1.8 nF). These capacitors increase the EMC robustness of the device. In 12 V applications it is further recommended to use a serial resistor R_{Supply} of 100 Ω (tbd) for protection on the supply line. A pull-up resistor R_{Load} is mandatory on the output pin and determines the maximum current flowing through the output transistor. A value of 1.2 k Ω is recommended for the 5V application. (see **Figure 1**)



Figure 1 Typical Application Circuit



Functional Description

1 Functional Description

The differential Hall sensor IC detects the motion of tooth and magnet encoder applications. To detect the motion of ferromagnetic objects, the magnetic field must be provided by a back biasing permanent magnet. Either south or north pole of the magnet can be attached to the rear unmarked side of the IC package (See **Figure 2**). The magnetic measurement is based on three equally spaced Hall elements, integrated on the IC. Both magnetic and mechanical offsets are cancelled by a self calibration algorithm.

1.1 Definition of the Magnetic Field Direction

The magnetic field of a permanent magnet exits from the north pole and enters the south pole. If a north pole is attached to the backside of the High End Transmission Sensor, the field at the sensor position is positive, as shown in **Figure 2**.



Figure 2 Definition of the Positive Magnetic Field Direction

1.2 Block Diagram



Figure 3 Block Diagram



Functional Description

1.3 Basic Operation

The speed signal calculated out of the differential hall elements, is amplified, filtered and digitized. An algorithm in the digital core for peak detection and offset calculation will be executed. The offset is fed back into the speed signal path with a digital to analog converter for offset correction. During uncalibrated mode, the output of the speed pulse is triggered in the digital core by exceeding a certain threshold of the tracking ADC. In calibrated mode the output is triggered by the visible hysteresis.

The direction signal is calculated out of center Hall signals. The direction signal is amplified, filtered, and digitized. In the digital core the direction and the vibration detection information is determined and the output protocol is issued.

1.4 Uncalibrated and Calibrated Mode

After power on the differential magnetic speed signal is tracked by an analog to digital converter (Tracking ADC) and monitored within the digital core. If the signal slope is identified as a rising edge or falling edge, the first output pulse is triggered. A second trigger pulse is issued with direction information.

In uncalibrated mode, the output protocols are triggered by the DNC (detection noise constant) in the speed path. After start up the sensor switches with the DNC min value and after that the DNC is adapted to the magnetic input signal amplitude.

The offset update starts if two valid extrema values are found and the direction of the update has the same orientation as the magnetic signal. For example, a positive offset update is being issued on a rising magnetic edge only. After a successful offset correction, the sensor is in calibrated mode. Switching occurs at the adaptive hysteresis threshold level.

In calibrated mode, the DNC is adapted to magnetic input signal amplitude with a minimum of ΔB_{limit} . The output pulses are then triggered with adaptive hysteresis.

1.5 Hysteresis Concept

The adaptive hysteresis is linked to the input signal. Therefore, the system is able to suppress switching if vibration or noise signals are smaller than the adaptive hysteresis levels. The minimum hysteresis level is ΔB_{limit} .



The visible hysteresis keeps the excellent performance in large pitch transmission application wheels.

Figure 4 Adaptive Hysteresis



Functional Description

1.6 Rotational Direction

The direction signal is digitized by an analog to digital converter (direction ADC) and fed into the digital core. Depending upon the rotation direction of the target wheel, the signal of the center probe anticipates or lags behind for 90°. This phase relationship is evaluated and converted into rotation direction information by sampling the signal of the center probe in the proximity of the zero crossing of the "speed" bridge signal.

The first pulse after power (power on pulse) has a different length to signalize that there is no direction information available.

Forward pulse (t_{fwd}) is issue if the wheel rotates from pin 1 to pin 3

Backward pulse (t_{bwd}) is issue if the wheel rotates from pin 3 to pin 1

Forward/backward pulse length could be inverted via EEPROM settings.



Figure 5 Direction definition

In case of high speed has been enable, the direction detection is switched off as soon as the frequency reach 4.3 kHz. To enter or leave the high frequency, two consecutive periods have to be larger or smaller than the frequency limit. this may delay the high frequency pulse at power on.

1.7 Vibration Suppression

The magnetic signal amplitude and the direction information are used for detection of parasitic magnetic signals. Unwanted magnetic signal can be caused by angular or air gap vibrations. If an input signal is identified as a vibration the output pulse will be suppressed.



General Characteristics

2 General Characteristics

2.1 Absolute Maximum Ratings

Table 2	Absolute Maximum Ratings
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Parameter	Symbol	Values			Unit	Note or Test Condition
		Min.	Тур.	Max.		
Supply voltage without	V _{DD}	-16	-	18	V	continuous, T _J ≤175°C
supply resistor				27	V	max. 60 s, $T_{\rm J} \le 175^{\circ} \rm C$
		-18			V	max. 60 s, $T_{\rm J} \le 175^{\circ} \rm C$
Output OFF voltage	V _{Q_OFF}	-1.0	-		V	max. 1 h, $T_{Amb} \le 40^{\circ}C$
		-0.3	-	26.5	V	continuous, $T_{\rm J} \le 175^{\circ} \rm C$
Output ON voltage	V _{Q_ON}	-	-	16	V	continuous, T _{Amb} ≤ 40°C
		-	-	18	V	max. 1 h, $T_{Amb} \le 40^{\circ}C$
		-	-	26.5	V	max. 60 s, <i>T</i> _{Amb} ≤ 40°C
Junction temperature range	TJ	-40	-	185	°C	exposure time: max. 10×1 h, $V_{DD} = 16V$
Magnetic field induction	B _Z	-5	-	5	Т	magnetic pulse during magnet magnetization valid 10 s with T _{ambient} ≤ 80°C
ESD compliance	ESD _{HBM}	-6	-	6	kV	HBM ¹⁾

1) ESD susceptibility, HBM according to EIA/JESD 22-A114B

Note: Stresses above the max values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.



General Characteristics

2.2 Operating Range

All parameters specified in the following sections refer to these operating conditions unless otherwise specified.

Table 3General Operating Conditions

Parameter	Symbol		Value	s	Unit	Note or Test Condition	
		Min. Typ.		Max.			
Supply voltage without supply resistance R _s	V _{DD}	4.0	-	16	V		
Continuous Output Off voltage	V _{Q_OFF}	-	-	16	V		
Supply voltage power- up/down voltage ramp	<i>dV</i> _{DD} /dt	3.0	-	1e4	V/ms		
Supply current	I _{DD}	8.0	-	13.4	mA		
Continuous output On current	I _{Q_ON}		-	15	mA	V _{Q_LOW} < 0.5 V	
Capacitance between IC supply & ground pins	C _{VDD}	198	220	242	nF	capacitor type X8R, rated voltage =50 V ¹⁾	
Dutput capacitance between IC putput and ground pins	C _Q	1.62	1.8	1.98	nF	capacitor type X8R, rated voltage =50 V ¹⁾	
Magnetic signal frequency range	f	0	-	10	kHz		
Frequency range for direction detection (hystersis)once high	f _{Dir}	0	-	4.3	kHz	increasing rotational frequency	
speed has been selected		0	_	4	kHz	decreasing rotational frequency	
Maximum number of EEPROM programming cycles	N _{PROG}			100	n		
Dynamic range of the magnetic field of the differential speed channel	DR _{mag_field_s}	-120	-	120	mT		
Dynamic range of the magnetic field of the direction channel	DR _{mag_field_dir}	-60	-	60	mT		
Static range of the magnetic field of the outer Hall probes in back-bias configuration	SR _{mag_field_s}	0	-	550	mT		
Static range of the magnetic field of the center Hall probe	DR _{mag_field_dir}	-100	-	450	mT		
Allowed static difference between outer probes	SR _{mag_field_diff}	-30	-	30	mT		
Normal operating junction cemperature	TJ	-40	-	175	°C	exposure time: max. 250 at <i>T</i> _J = 175°C, <i>V</i> _{DD} = 16 V	
		-	-	185	°C	exposure time: max. 10×1 h at $T_{J} = 185^{\circ}$ C, $V_{DD} = 16$ V, additive to other lifetime	



General Characteristics

Table 3General Operating Conditions (cont'd)

Parameter	Symbol		Values	5	Unit	Note or Test Condition
		Min.	Тур.	Max.		
Not operational lifetime	T _{no}	-40		150	°C	without sensor function. Exposure time max 500 h @ 150°C; increased time for lower temperatures according to Arrhenius- Model, additive to other lifetime
Ambient temperature range for device features reading and programming	T _{RDPROG}	15	25	130	°C	during programming at customer
Temperature compensation range of magnetic material	ТС		-600		ppm	internal compensation of magnetic signal amplitude of speed signal

1) Specified at room temperature, test condition at 25°C with 1V at 1kHz, temperature variation to be added

Note: In the operating range the functions given in the functional description are fulfilled



3 Electrical and Magnetic Characteristics

All values specified at constant amplitude and offset of input signal, over operating range, unless otherwise specified. Typical values correspond to $V_s = 5 V$ and $T_{Amb.} = 25^{\circ}C$

Parameter	Symbol		Values	;	Unit	Note or Test Condition
		Min.	Тур.	Max.		
Output saturation voltage	V _{Qsat}	0	-	500	mV	<i>I</i> _Q ≤ 15 mA
Clamping voltage V _{DD} -Pin	$V_{\rm DD_clamp}$	42		-	V	leakage current through ESD diode < 0.5mA
Clamping voltage V _Q -Pin	V _{Qclamp}	42		-	V	leakage current through ESD diode < 0.5mA
Reset voltage	V _{DD_reset}	2.8		3.6	V	
Output leakage current	I _{Qleak}	0	0.1	10	μA	V _Q = 18 V
Output current limit during short-circuit condition	I _{Qshort}	30	-	80	mA	
Junction temperature limit for output protection	T _{prot}	190	-	205	°C	
Power on time	t _{power_on}	0.8	0.9	1	ms	during this time the output is locked to high.
Delay time between magnetic signal switching point and corresponding output signal falling edge switching event	t _{delay}	10	14	19	μs	falling edge
Output fall time	t _{fall}	2.0	2.5	3.0	μs	$V_{Pullup} = 5 V, R_{Pullup} = 1.2 kΩ (+/-10\%), C_Q = 1.8 nF (+/-15\%),$ valid between 80% - 20%
		3.2	4.5	5.8	μs	$V_{Pullup} = 5 V, R_{Pullup} = 1.2 kΩ (+/-10\%), C_Q = 1.8 nF (+/-15\%),$ valid between 90% - 10%
Output rise time	t _{rise} ¹⁾	4	-	11.4	μs	$R_{Pullup} = 1.2 \text{ k}\Omega (+/-10\%),$ $C_Q = 1.8 \text{ nF} (+/-15\%),$ valid between 10% - 90%
Digital noise constant of speed channel during start up	DNC _{min}	1.22	1.5	1.78	mT	
Adaptive hysteresis threshold	HYS _{adaptive}	-	25	-	%	EEPROM "HYST_ADAPT"Option 0
		-	12.5	-	%	EEPROM "HYST_ADAPT"Option 1
Period Jitter, $f \le 8 \text{ kHz}^{2}$	Jit _{8kHz}	-1	-	1	%	1 sigma, ΔB _{pkpk} = 3mT
Period Jitter, $8 \text{ Hz} \le f \le 10 \text{ kHz}^{2}$	Jit _{10kHz}	-1.1		1.1	%	1 sigma, ΔB _{pkpk} = 3mT
Number of wrong pulses at	n _{Start}	-	-	0	n	in forward rotational direction
start-up		0	-	1	n	in backward rotational direction



Parameter	Symbol		Values	5	Unit	Note or Test Condition
		Min.	Тур.	Max.		
Global run out ³⁾	Runout _{glob} al,speed	0	-	40	%	of magnetic speed signal amplitude
		0	-	60	%	of magnetic speed signal amplitude with reduced performance on stand-still functionality
	Runout _{glob} al,dir	0	-	40	%	of magnetic direction signal amplitude
		0	-	60	%	Of magnetic direction signal amplitude with reduced performance on stand-still functionality
Tooth to tooth run out (peak to peak variation on two	Runout _{tooth}	0	-	40	%	of magnetic speed signal amplitude
consecutive teeth / pole-pair) ³⁾	Runout _{tooth}	0	-	40	%	of magnetic direction signal amplitude

Table 4Electrical and Magnetic Parameters (cont'd)

1) Value of capacitor: 1.8 nF±10%; ceramic: X8R; maximum voltage: 50 V

- 2) Parameter not subject to productive test. Verified by lab characterization based on jitter-measurement > 1000 periods
- 3) Defined as 1-(amplitude_min/amplitude_max)
- Note: The listed Electrical and magnetic characteristics are ensured over the operating range of the integrated circuit. Typical characteristics specify mean values expected over the production spread. If not other specified, typical characteristics apply at $T_{Amb} = 25^{\circ}$ C and $V_{s} = 5 V$.

3.1 Output protocols

TLE4959C FX provides the option to select output protocol without direction detection. As well as the following direction detection options where the direction is provided via PWM protocol.

Parameter	Symbol	Values			Unit	Note or Test Condition
		Min.	Тур.	Max.		
Output pulse in forward direction	t _{fwd}	38	45	52	μs	
Output pulse in backward direction	t _{bwd}	114	135	155	μs	
Power on pulse	t _{power-on}	153	180	207	μs	

Table 5 Option 1



Table 5Option 1 (cont'd)

Parameter	Symbol		Values			Note or Test Condition
		Min.	Тур.	Max.		
Output pulse at High speed	t _{high_speed}	25.5	30	34.5	μs	pulse available after High speed option has been selected
Stand still pulse	t _{stand-still}	51	60	69	μs	pulse available stand still after pulse option has been selected. Pulse delivered if no relevant magnetic signal change has been detected within 50ms

Note: $V_{Pullup} = 5 V$, *RPullup* = 1.2 k Ω (+/-10%), *CQ* = 1.8 nF (+/-15%), valid between 50% of falling edge to 50% of next rising edge

Table 6 Option 2

Parameter	Symbol	Symbol Values				Note or Test Condition
		Min.	Тур.	Max.		
Output pulse in forward direction	t _{fwd}	38	45	52	μs	
Output pulse in backward direction	t _{bwd}	153	180	207	μs	
Output pulse at High speed	t _{high_speed}	38	45	52	μs	pulse available after High speed option has been selected

Attention: First pulse after magnetic edge suppressed

Note: $V_{Pullup} = 5 \text{ V}$, *RPullup* = 1.2 k Ω (+/-10%), *CQ* = 1.8 nF (+/-15%), valid between 50% of falling edge to 50% of next rising edge

Table 7 Option 3

Parameter	Symbol	Values			Unit	Note or Test Condition
		Min.	Тур.	Max.		
Output pulse in forward direction	t _{fwd}	51	60	69	μs	
Output pulse in backward direction	t _{bwd}	102	120	138	μs	
Power on pulse	t _{power-on}	25.5	30	34.5	μs	
Output pulse at High speed	$t_{\sf high_speed}$	25.5	30	34.5	μs	pulse available after High speed option has been selected



Note: $V_{Pullup} = 5 V$, *RPullup* = 1.2 k Ω (+/-10%), *CQ* = 1.8 nF (+/-15%), valid between 50% of falling edge to 50% of next rising edge

Table 8 Option 4

Parameter	Symbol		Values		Unit	Note or Test Condition	
		Min.	Тур.	Max.			
Output pulse in forward direction	t _{fwd}	38	45	52	μs		
Output pulse in backward direction	t _{bwd}	76.5	90	103.5	μs		
Power on pulse	t _{power-on}	153	180	207	μs		
Output pulse at High speed	t_{high_speed}	38	45	52	μs	pulse available after High speed option has been selected	

Note: $V_{Pullup} = 5 V$, *RPullup* = 1.2 k Ω (+/-10%), *CQ* = 1.8 nF (+/-15%), valid between 50% of falling edge to 50% of next rising edge



EEPROM Functional Description

4 EEPROM Functional Description

4.1 Serial Interface

The serial interface is used to set parameter and to program the sensor IC, it allows writing and reading of internal registers. Data transmission to the IC is done by supply voltage modulation, by providing the clock timing and data information via only one line. Data from the IC are delivered via the output line, triggered by as well clocking the supply line. In normal application operation the interface is not active, for entering that mode a certain command right after power-on is required.

A detailed document (TLE4959C FX EEPROM Programming Guide) is available on request. It contains the description of electrical timing and voltage requirements, as well as the information about data protocol, available registers and addresses.

4.1.1 Data Transmission

Commands to the sensor are sent by modulating the supply voltage between two levels $V_{DD,high}$ and $V_{DD,low}$. They are sent in series of 17 pulses corresponding to 16 bit words, with MSB transmitted first and LSB last, respectively the stop bit. Each of the 16 pulses is coded by the duty cycle as logical "0" or "1". Logical "1" is represented by a duty cycle of 2/3 of the period on $V_{DD,high}$, logical "0" is represented by a duty cycle of 1/3 at $V_{DD,high}$. This forms the bit information and acts also as serial interface clock. Data transmission from the device is represented by the state of the output, high for logical "1" and low for logical "0". Recommended period length is around 200 (tbd) μ s per bit.

End of word is indicated by a long "low" supply (> 750 ms, first 30 ms should be > $V_{DD,high}$, remaining time < $V_{DD,low}$). Please note, that for transmission of 16 data bits in total 17 pulses on V_{DD} are necessary. If more than 16 input bits are transmitted the output bits are irrelevant (transmission buffer empty), whereas the input bits remain valid and start overwriting the previously transmitted bits. In any case the last 17 transmitted bits are interpreted as transmitted data word (16 bit) + 1 stop bit.



Figure 6 Serial Protocol



EEPROM Functional Description

4.2 **EEPROM Description**

Several options of TLE4959C FX can be programmed via an EEPROM to optimize the sensor algorithm to the individual target wheel and application requirements. The EEPROM memory is organized in 2 customer lines. Each line is composed of 16 data bits and additional 6 bits for error detection and correction, based on ECC (Error Correction Code). For more detailed information about EEPROM access and programming an additional document is available on request.

Table 9	EEPROM Address 0x0

15 14 13 12 11 10 9 8 7 6 5 4 3 2 1 0	1 4510	5														
	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0

Field	Bit	Туре	Description	TLE4959C FX		
Not used	15	r	Always read as "0"	0		
Not used	14	rw	To be set to "0"	0		
HIGH_SPEED	13	rw	0 = Enabled motion detection 1 = According selected protocol when above 4.3kHz	0		
Not used	12	rw	To be set to "0"	0		
STAND_EN	11	rw	0=disable stand-still pulse 1=enable stand-still pulse Stand still pulse is provided, if enabled, only if PW_CHIOICE=00	0		
Not used	100	rw	To be set to "0000000000"	0000000000		

Table 10Functional Description Address 0x0

Table 11EEPROM Address 0x1

15 14 12 12 11 10 0 0 7 6 5 4 2 2 1 0																
	15	14	T D	12	11	10	9	8	7	6	5	4	3	2	1	0

Table 12Functional Description Address 0x1

Field Bit		Туре	Description	TLE4959C FX	
Not used	15:14	rw	To be set to "01"	01	
PW_CHOICE	13:12	rw	Choice of PWM protocol for direction detection. 00 = Option 1 01 = Option 2 10 = Option 3 11 = Option 4	11	
FORWARD_DEF	11	rw	0 = None invertion of forward definition 1 = Invertion of forward definition	0	
EDGE_POLAR	E_POLAR 10 rw 0 = None invertion 1 = Invertion		0		
HYST_ADAPT	9	rw	0 = 25% 1 = 12.5%	1	



EEPROM Functional Description

Field	Bit	Туре	Description	TLE4959C FX	
Not used	8 5	rw	To be set to "1101"	1101	
DNC_ADAPT	4	rw	DNC Adaption: 0 = 25% 1 = 12.5%	0	
Not used	3	rw	To be set to "0"	0	
DIR_ENABLE	2	rw	0 = Direction detection off 1 = Direction detection on	1	
Not used	1	rw	To be set to "1"	1	
LOCK	0	rw	0 = User area of EEPROM is unlocked 1 = User area of EEPROM is locked (no reprogramming possible)	0	

Table 12 Functional Description Address 0x1 (cont'd)



Package Information

5 Package Information

Pure tin covering (green lead plating) is used. The product is RoHS (Restriction of Hazardous Substances) compliant and marked with letter G in front of the data code marking and may contain a data matrix code on the rear side of the package (see also information note 136/03). Please refer to your key account team or regional sales if you need further information.

The specification for soldering and welding is defined in the latest revision of application note "Recommendation for Board Assembly-Hallsensor SSO Packages".

5.1 Package Outline



Figure 7

7 PG-SSO-3-52 (Plastic Green Single Slim Outline), Package Dimensions



Package Information

5.2 Position of the Hall Element





5.3 Marking and Data Matrix Code





5.4 Pin Configuration and Sensitive Area

Table 13 Pin Description

Pin Number ¹⁾	Symbol	Function
1	V _{DD}	Supply Voltage
2	GND	Ground
3	Q	Open Drain Output

1) Refer to frontside view: leftmost pin corresponding to pin number 1



Package Information

5.5 Packing Information



Figure 10 PG-SSO-3-52 Ammopack



Revision History

6 **Revision History**

Revision	Date	Changes
1.0	2017-10-05	First version of released datasheet

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